

#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Continuous Collector Current	I <sub>C</sub>	-0.5	Α
Peak Collector Current	I <sub>CM</sub>	-1.0	Α
Peak Base Current	I <sub>BM</sub>	-200	mA

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 6)	D-	310	mW	
Fower Dissipation	(Note 7)	$P_{D}$	350		
Thermal Resistance, Junction to Ambient	(Note 6)	D	403	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	357	C/VV	
Thermal Resistance, Junction to Leads	(Note 8)	$R_{ heta JL}$	350	°C/W	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

#### **ESD Ratings** (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	≥ 8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	С

Notes:

- 6. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition; device measured when operating in steady state condition.

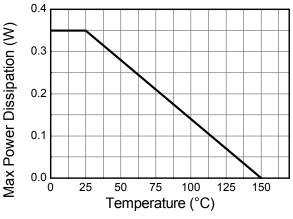
  7. Same as Note 6, except the device is mounted on 15mm X 15mm FR4 PCB.

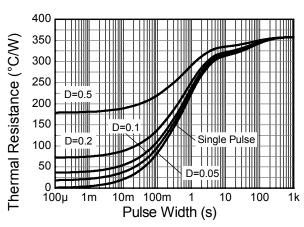
  8. Thermal resistance from junction to solder-point (at the end of the leads).

  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



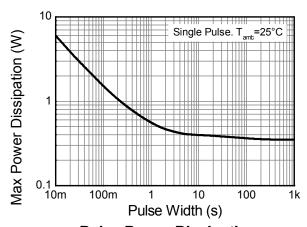
# **Thermal Characteristics and Derating Information**





**Derating Curve** 

**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV <sub>CBO</sub>	-50	_	_	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage		BV <sub>CEO</sub>	-45	_	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage		BV <sub>EBO</sub>	-5	_	_	V	I <sub>C</sub> = -100μA
Collector-Emitter Cutoff Current		I <sub>CES</sub>	_	_	-100 -5.0	nΑ μΑ	V <sub>CE</sub> = -45V V <sub>CE</sub> = -25V, T <sub>J</sub> = +150°C
Emitter-Base Cutoff Current		I <sub>EBO</sub>	_	_	-100	nA	V <sub>EB</sub> = -5.0V
DC Current Gain (Note 10)	BC807-16 BC807-25 BC807-40	- h <sub>FE</sub>	100 160 250		250 400 600	_	V <sub>CE</sub> = -1.0V, I <sub>C</sub> = -100mA
	BC807-16 BC807-25 BC807-40		60 100 170	_	_		V <sub>CE</sub> = -1.0V, I <sub>C</sub> = -300mA
Collector-Emitter Saturation Voltage (Note 10)		V <sub>CE(SAT)</sub>	_	_	-0.7	V	I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Base-Emitter Voltage (Note 10)		V <sub>BE</sub>	_	_	-1.2	V	V <sub>CE</sub> = -1.0V, I <sub>C</sub> = -300mA
Gain Bandwidth Product		f <sub>T</sub>	100	_	_	MHz	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA, f = 50MHz
Collector-Base Capacitance		C <sub>CBO</sub>	_	_	12	pF	V <sub>CB</sub> = -10V, f = 1.0MHz

Note:

10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%



# Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

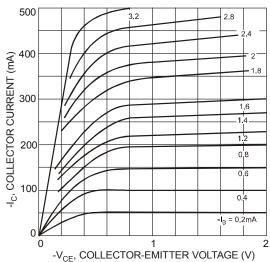


Figure 1 Typical Collector Current vs. Collector-Emitter Voltage

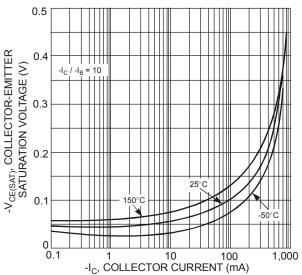
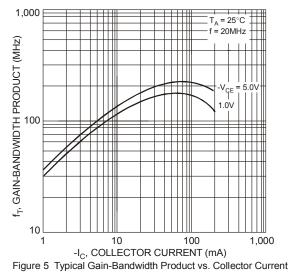


Figure 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current



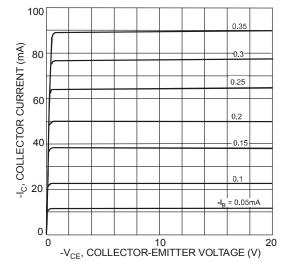


Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

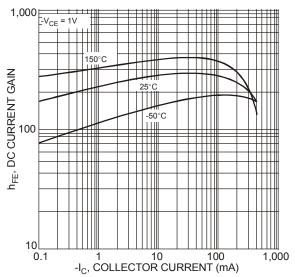
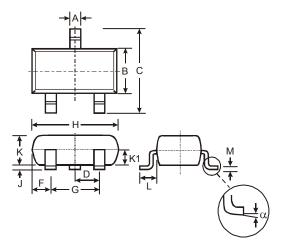


Figure 4 Typical DC Current Gain vs. Collector Current



### **Package Outline Dimensions**

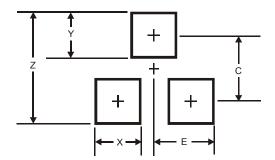
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SOT23					
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.903	1.10	1.00			
K1	-	1	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Υ	0.9
С	2.0
E	1.35



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